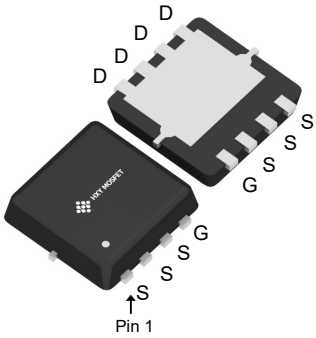
DMT35M4LFVW-7

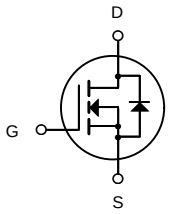
N-SGT Enhancement Mode MOSFET

Description

The DMT35M4LFVW-7 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness.



DFN3X3-8L



N-Channel MOSFET

General Features

V_{DS} =30V I_D = 40A

$R_{DS(ON)}$ < 6.3mΩ@ V_{GS}=10V

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMT35M4LFVW-7	DFN3X3-8L	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25°C unless therwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	28	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	27	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	24	A
I_{DM}	Pulsed Drain Current[2]	135	A
EAS	Single Pulse Avalanche Energy[3]	29.8	mJ
I_{AS}	Avalanche Current	27	A
P_D@T_C=25℃	Total Power Dissipation[4]	30	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	4.6	℃/W

Electrical Characteristics(T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	5	6.3	mΩ
		V_{GS}=4.5V , I_D=15A	---	6.9	9	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	67	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=15A	---	8	---	nC
Q_{gs}	Gate-Source Charge		---	2.4	---	
Q_{gd}	Gate-Drain Charge		---	3.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=15A	---	7.1	---	ns
T_r	Rise Time		---	40	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	814	---	pF
C_{oss}	Output Capacitance		---	498	---	
C_{rss}	Reverse Transfer Capacitance		---	41	---	
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	40	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1	V
t_{rr}	Reverse Recovery Time	I_F=20A , di/dt=100A/μs , T_J=25°C	---	15	---	nS
Q_{rr}	Reverse Recovery Charge		---	25	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=24A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

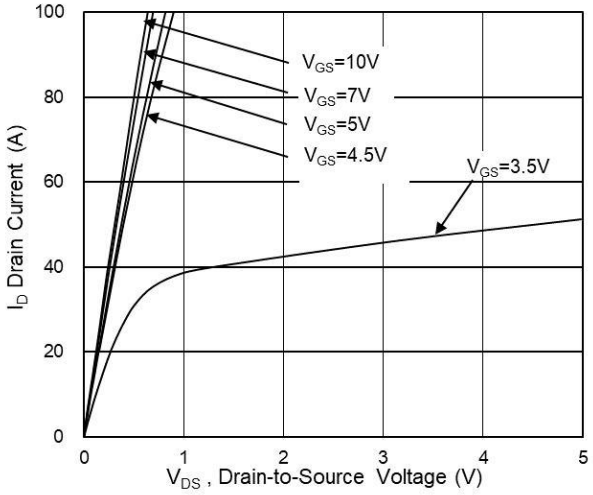


Fig.1 Typical Output Characteristics

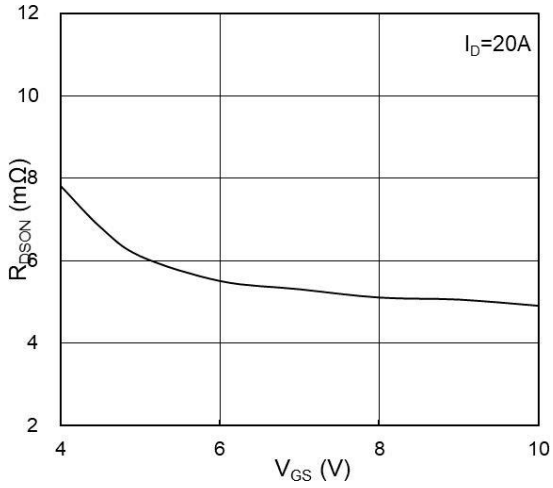


Fig.2 On-Resistance vs G-S Voltage

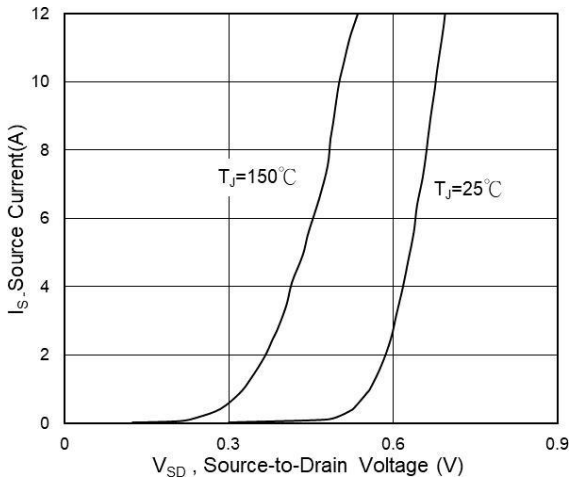


Fig.3 Source Drain Forward Characteristics

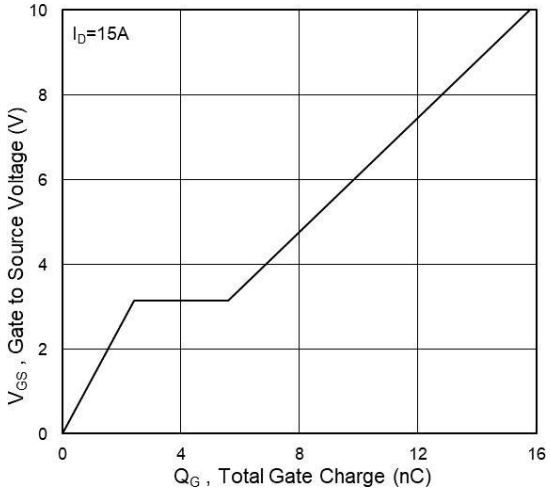


Fig.4 Gate-Charge Characteristics

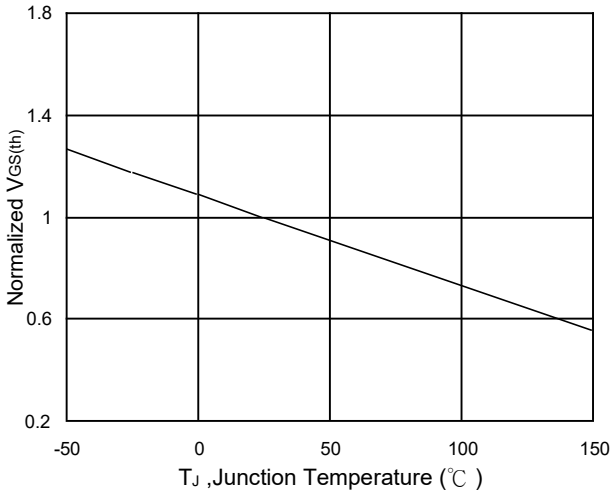


Fig.5 Normalized $V_{GS(th)}$ vs T_J

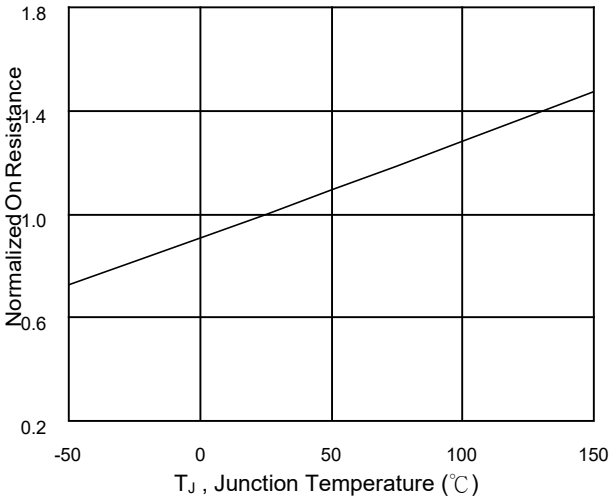


Fig.6 Normalized R_{DSON} vs T_J

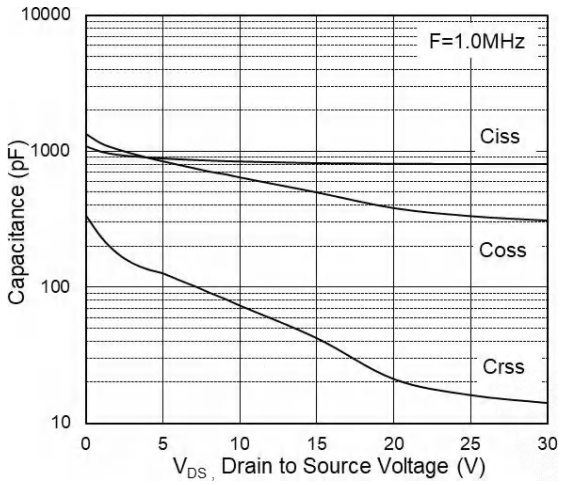


Fig.7 Capacitance

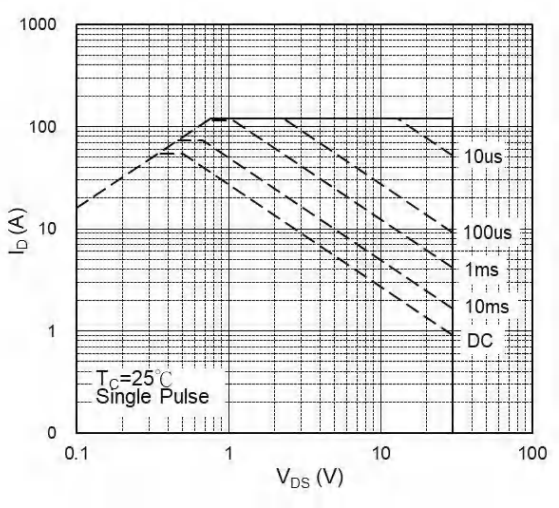


Fig.8 Safe Operating Area

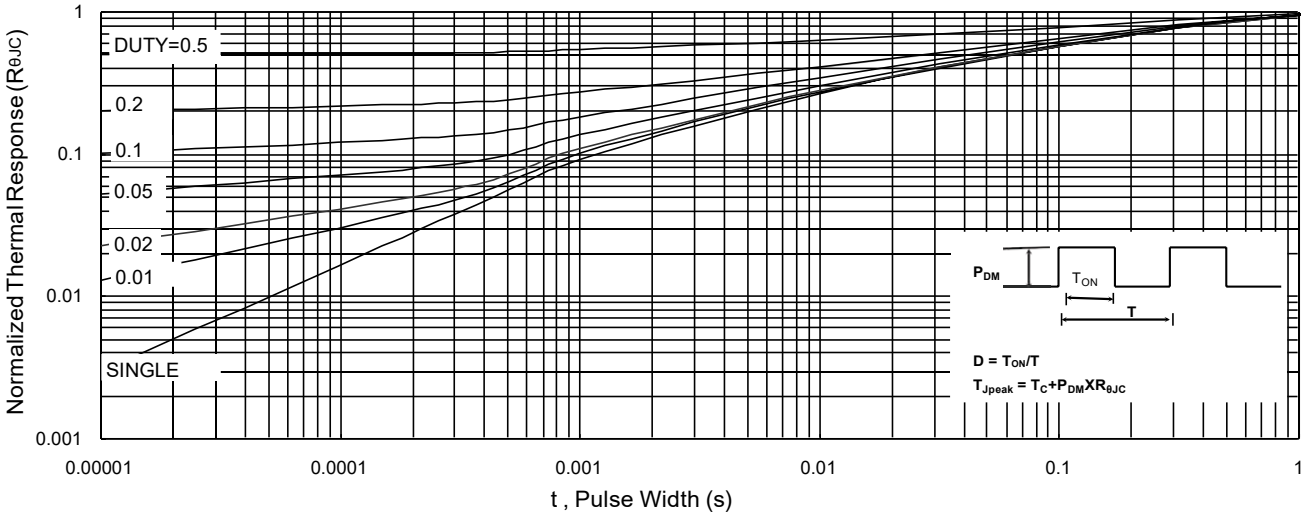


Fig.9 Normalized Maximum Transient Thermal Impedance

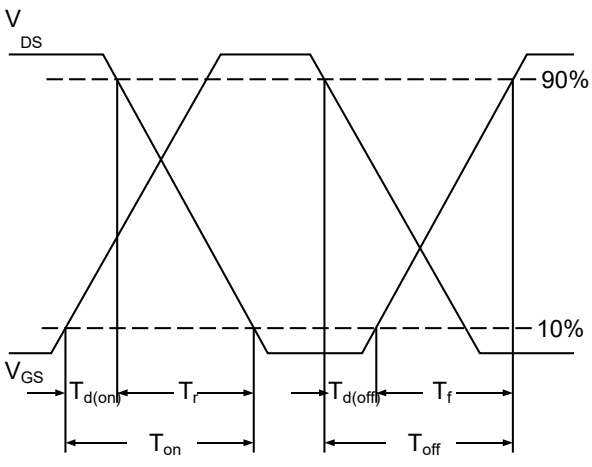


Fig.10 Switching Time Waveform

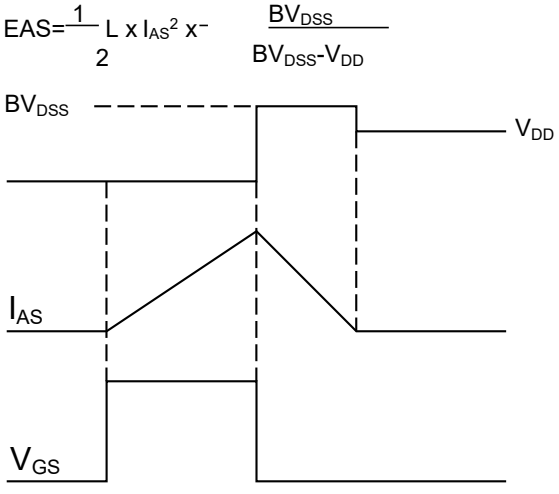
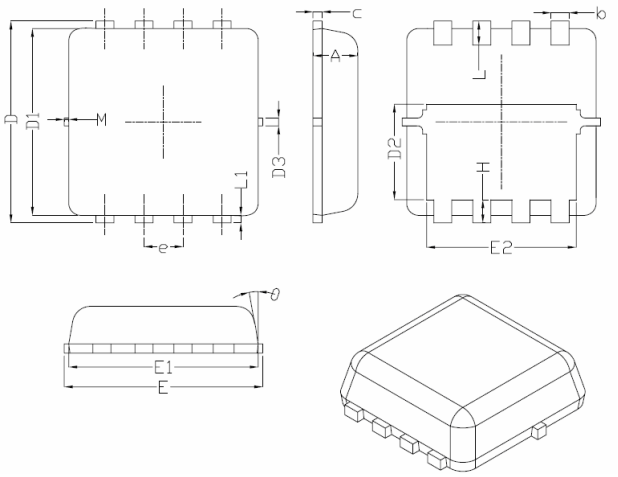


Fig.11 Unclamped Inductive Switching Waveform

DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

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